Probing Materials' Behavior using Fast Electrons

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Workshop on Ultrafast Dec 9-12, 2013, Key West, FL





180° ferroelectric domain wall in multiferroic ErMnO₃

Er Mn O

D

P_s

1 nm

MG. Han /BNL



Krivanek et al, Nature (2010)

Imaging atoms

Single Si atom on graphene



Single BN layer



red: B; yellow: C; green: N; blue: O

EELS mapping: La_{0.7}Sr_{0.3}MnO₃/SrTiO₃



Muller et al Science 319, 1073 (2008)





Krivanek et al, Nature (2010)

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Thermal Magnetic Field Noise Limits Resolution in Transmission Electron Microscopy

Stephan Uhlemann,^{*} Heiko Müller, Peter Hartel, Joachim Zach, and Max. Haider CEOS Corrected Electron Optical Systems GmbH, Englerstraße 28, 69126 Heidelberg, Germany (Received 6 May 2013; published 22 July 2013)

Atomic surface imaging with secondary electrons

 $SrTiO_3$



Atomic surface imaging with secondary electrons

Zhu, et al, Nature Materials, 8, 808 (2009)







Imaging surface U atoms



Uniqueness of electron scattering

Sensitive to valence electrons at small scattering angles



Direct Imaging of Charge Modulation

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J. Tafto

Department of Physics, University of Oslo, P.O. Box 1048, 0316 Blindern, Oslo 3, Norway (Received 7 September 1995)



Picometer Accuracy in Measuring Lattice Displacements Across Planar Faults by Interferometry in Coherent Electron Diffraction

Lijun Wu, Yimei Zhu,* and J. Tafto[†]

Materials Science Division, Brookhaven National Laboratory, Upton, New York 11973 (Received 12 June 2000)



$$\varphi_{g} = \sum_{m,n} F_{g} \exp 2\pi i \left(\frac{\sqrt{r^{2} + H^{2}}}{\lambda} - \vec{r} \cdot \vec{g} \right)$$



Picometer Accuracy in Measuring Lattice Displacements Across Planar Faults by Interferometry in Coherent Electron Diffraction Lijun Wu, Yimei Zhu, and J. Tafto Phys. Rev. Lett. 85, 5126 (11 December 2000)

The Most Accurate Defect Measurement

11 December 2000

Fault lines between pure crystals affect con properties of semiconductors in computer c them precisely. A new technique, reported i electron beam to measure so-called stacking meter (1 pm), ten times better than previous purity of a coherent electron beam, the auth transmitted through large regions of pure cr technique may improve understanding of cr with material properties.

Conventional electron microscopes use inconerent bear heating a filament, so the electron waves originating fn filament are not synchronized. But coherent beams con from which the electrons are liberated by an electric fit coherently from such a source, just as light streaming t is more coherent than that of a lightbulb. Coherent elec become commercially available in just the past five yet

With improvements in coherent electron sources has co structures. The latest system, developed by Yimei Zhu uses one of the best electron microscopes in the world, the measurement does not





Accuracy : 0.01 Å

12 To make the measurement otherwise high quality this 10 $F_g^e \sim f_g^e \exp\left[2\pi i g \cdot (r + \Delta r)\right]$ Structure Factor ∆F 8 6 Ba₂Sr₂CaCu₂O₈ 2 0 (000)(050)(0100)(0150)(0200)Reflections

Imaging electrons, spins, electromagnetic potentials

Valence electron distribution

charge density ρ :

$$\rho(r) = \frac{1}{\Omega} \sum_{g} F_{g}^{x} \exp(2\pi i g \cdot r)$$

structure factor

 $\rho = -\nabla^2 V \varepsilon_0$

Electrostatic and magnetic potential distribution

electrostatic potential V magnetic potential B :

$$\phi(r) = C_E \int V(r,z) dz - \int \frac{e}{\hbar} \vec{A}(r,z) \cdot d\vec{r}$$

Aharonov-Bohm phase shift of the wave function

Mapping valence electron distribution with quantitative diffraction

$$\rho(r) = \frac{1}{\Omega} \sum_{g} F_{g}^{x} \exp(2\pi i g \cdot r)$$

$$F - F_{IAM} \longrightarrow FFT$$



CaCu₃Ti₄O₁₂: PRL 99 037602 (2007)



Experiment : ED + X-ray, 90K



DFT, w/o disorder



Probing bonding states and charge transfer with EELS

2-D Electron Gas: $SrTiO_3/RO/SrTiO_3$ (R=La, Pr, Nd, Sm, Y)



In collaboration with Prof. C.B Eom

Jang et al Science, <u>311</u>, 886 (2011)

Probing bonding states and charge transfer with EELS

2-D Electron Gas: $SrTiO_3/RO/SrTiO_3$ (R=La, Pr, Nd, Sm, Y)



Ondrej Krivanek

Direct imaging of ferroelectric order using holography

- RT ferroelectric order can be down to 10-15nm, below 10nm superparaelectric.

BaTiO₃ Curie temperature 130°C

Polking, Han, et al, Nat. Mat., **11** 700 (2012)



Direct observation of the Lithiation process in Li-ion-batteries





$FeF_2 + 2Li^+ + 2e^- \rightarrow 2LiF + Fe$







Wang et al Nature Comm. <u>3</u>, 1201 (2012)

Can we image individual spins?

For BCC Fe NP, the max phase shift is ~50urad, 10^{-3} of $2\pi/100$



| | EH | LM | MFM | SP-STM | n | MOKE | X-rays |
|--------------------|--|---|--------------------|---|--|------------------------|------------------------|
| Strength | Mapping fields, measuring moments | Quick and easy, large field of view | Easy, cheap | Single-spin sensitivity, manipulation | Resolving unknown spin structures, spin wave Q(w) | Super fast dynamics | Super fast dynamics |
| Weakness | Requires practice | Qualitative | Perturbs sample | Surface-only | Bulk/crystal- only, requires a neutron source | Surface- only | Requires a synchrotron |
| Time resolution | 100 ms | 10 ms | 1 s | 1 s | n/a | 1 fs | 1 fs |
| Spatial resolution | 3 nm | 10 nm | 50 nm | 0.1 nm | n/a | 100 nm | 20 nm |
| Sensitivity | π/100 rad phase shift | 1 μrad deflection | 100 pN force | <1 µ _B moment | <1 μ_B moment | 20 μrad rotation | ? |

Phase plate for magnetic imaging



www.Jeolusa.com

Imaging magnetic moments



Imaging vortex-precession orbit via resonance excitation





Vortex dynamics in nanomagnet



2um Py square

Pollard et al Nature Comm. **3** 1028 (2012)

Imaging vortex-precession orbit via resonance excitation



Our goals: understanding strongly correlated materials

Challenges:

Coupling electronic-lattice system

 \rightarrow charge, orbital and spin order

Strong interplay between charge, spins, orbital and lattice

 \rightarrow complex phase diagrams, exotic material properties



One solution:

Decouple the subsystems in the time domain and then observe the dynamics of subsystems separately.

<u>Ultrafast ED</u>: better time resolution & simultaneously observe diverse degrees of freedom.

Ultrafast electron diffraction at BNL

Currently optimized at 2.8MeV with 120fs resolution

- 2-4 MeV electron energy
- 100 fs pulse, Hz repetition rate -
- 10⁶ electrons in a single pulse -
- energy spread <0.01%
- 30urad divergence
- beam size on detector 200um
- Synchronization of RF & laser <50fs
- cryogenic capability
- longitudinal coherence length 1-2nm
- transverse coherence length ~10nm



XJ Wang's talk Monday morning

2H-TaSe₂



SP intensity reduced to ~ 0, without obvious recovery in the following 50 ps Coherent phonon: 2.5THz (~ 400fs)

P. Zhu et al, APL 2013

Ultrafast electron diffraction for spin dynamics ?



Acknowledgement

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